



NeoEE

100,000+ Times MTP IP

eMemory's NeoEE is an EEPROM solution using floating gate technology, with endurance up to 500K cycles. The IP is tailored for applications requiring high endurance and low power. Both program and erase are achieved by reliable Fowler-Nordheim tunneling mechanism.



High Yield

Suitable for major foundries using CMOS technologies



Fast Time to Market

No process tuning, easy porting to derivative processes



High Reliability

AEC-Q100 Grade 0 compliant
ISO26262 ASIL D certification



Low Power

Low current consumption for write and read operations

Highlights

- Industry's smallest logic process-based Kbits NVM device with 100K endurance
- No additional masking layer required
- 0.3μm~65nm



High Endurance

Robust F-N programming at wide VDD range

NeoMTP

1,000+ Times MTP IP

eMemory's NeoMTP is a multiple-time programmable memory solution using floating gate technology. The IP does not require additional mask layers or thermal budget for 3.3V IO or 5V IO devices. It can offer up to 1K endurance cycles at the industry's lowest implementation costs.



High Yield

Suitable for CMOS technologies in major foundries



Fast Time to Market

No process tuning or extra process required



High Temperature Storage

AEC-Q100 Grade 0 compliant



Wide Operation Temperature

-40°C ~175°C

Highlights

- Suitable for all logic-derivative CMOS technologies
- High Read speed (20~40ns), reasonable testing cost and writing code time
- 0.18μm~55nm



Wide Operation Voltage

40ns access speed for VDD=2.5V~5.5V